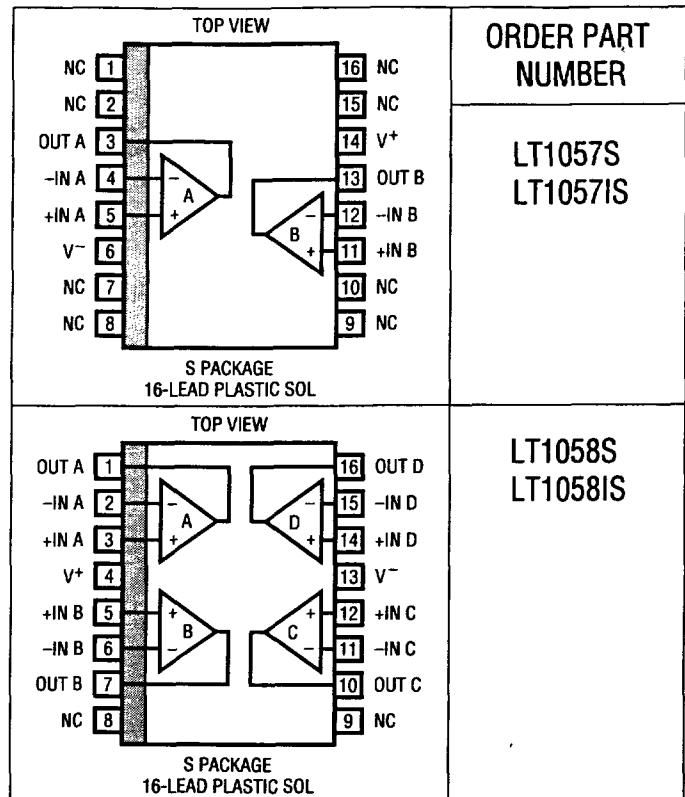


LT1057S/LT1057IS
 LT1058S/LT1058IS

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	±20V
Differential Input Voltage	±40V
Input Voltage	±20V
Output Short Circuit Duration	Indefinite
Operating Temperature Range	
LT1057S, LT1058S	0°C to 70°C
LT1057IS, LT1058IS	-40°C to 85°C
Storage Temperature Range	
All Devices	-65°C to 150°C
Lead Temperature (Soldering, 10 sec.)	300°C

PACKAGE/ORDER INFORMATION



ORDER PART NUMBER

LT1057S
 LT1057IS

LT1058S
 LT1058IS

ELECTRICAL CHARACTERISTICS $V_S = \pm 15V$, $T_A = 25^\circ C$, $V_{CM} = 0V$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{OS}	Input Offset Voltage	LT1057		0.3	2	mV
		LT1058		0.35	2.5	
I_{OS}	Input Offset Current	Fully Warmed Up		5	50	pA
I_B	Input Bias Current	Fully Warmed Up		±10	±100	pA
	Input Resistance – Differential – Common-Mode	$V_{CM} = -11V$ to $+8V$ $V_{CM} = +8V$ to $+11V$		0.4		Ω
				0.4		
				0.05		
	Input Capacitance			4		pF
e_n	Input Noise Voltage	0.1Hz to 10Hz	LT1057	2.1		μV_{p-p}
			LT1058	2.5		
e_n	Input Noise Voltage Density	$f_0 = 10Hz$ $f_0 = 1kHz$		26 13		nV/\sqrt{Hz}
i_n	Input Noise Current Density	$f_0 = 10Hz, 1kHz$		1.8		fA/\sqrt{Hz}
A_{VOL}	Large Signal Voltage Gain	$V_0 = \pm 10V$ $R_L = 2k$ $R_L = 1k$	100	300		V/mV
			50	220		
	Input Voltage Range		±10.5	14.3 -11.5		V

ELECTRICAL CHARACTERISTICS $V_S = \pm 15V$, $T_A = 25^\circ C$, $V_{CM} = 0V$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 10.5V$	LT1057	82	98	dB
			LT1058	80	98	
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10V$ to $\pm 18V$	86	102		dB
V_{OUT}	Output Voltage Swing	$R_L = 2k$	± 12	± 13		V
SR	Slew Rate		8	13		V/ μs
GBW	Gain-Bandwidth Product	$f = 1MHz$ (Note 1)	3	5		MHz
I_S	Supply Current Per Amplifier			1.7	2.8	mA
	Channel Separation	DC to 5kHz, $V_{IN} = \pm 10V$		130		

ELECTRICAL CHARACTERISTICS $V_S = \pm 15V$, $V_{CM} = 0V$, $0^\circ C \leq T_A \leq 70^\circ C$, (LT1057S, LT1058S) or $-40^\circ C \leq T_A \leq 85^\circ C$, (LT1057IS, LT1058IS), unless otherwise noted.

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{OS}	Input Offset Voltage	LT1057	•	0.5	2.5	mV	
		LT1058S	•	0.6	3.0		
		LT1058IS	•	0.7	4.0		
	Average Temperature Coefficient of Input Offset Voltage		•	5		$\mu V/^\circ C$	
I_{OS}	Input Offset Current	Warmed Up, $T_A = 70^\circ C$		20	250	pA	
		Warmed Up, $T_A = 85^\circ C$		35	400		
I_B	Input Bias Current	Warmed Up, $T_A = 70^\circ C$		± 60	± 400	pA	
		Warmed Up, $T_A = 85^\circ C$		± 100	± 700		
A_{VOL}	Large Signal Voltage Gain	$V_O = \pm 10V$, $R_L = 2k$ LT1057	•	50	200	V/mV	
		LT1058	•	40	200		
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 10.5V$	LT1057	•	80	96	dB
			LT1058	•	78	96	
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10V$ to $\pm 18V$	LT1057	•	84	100	dB
			LT1058	•	82	100	
V_{OUT}	Output Voltage Swing	$R_L = 2k$	•	± 12	± 12.8	V	

The • denotes the specifications which apply over the full operating temperature range.

Note 1: Gain bandwidth product is not tested. It is guaranteed by design and by inference from the slew rate measurement.